

NPN RF POWER TRANSISTOR

DESCRIPTION:

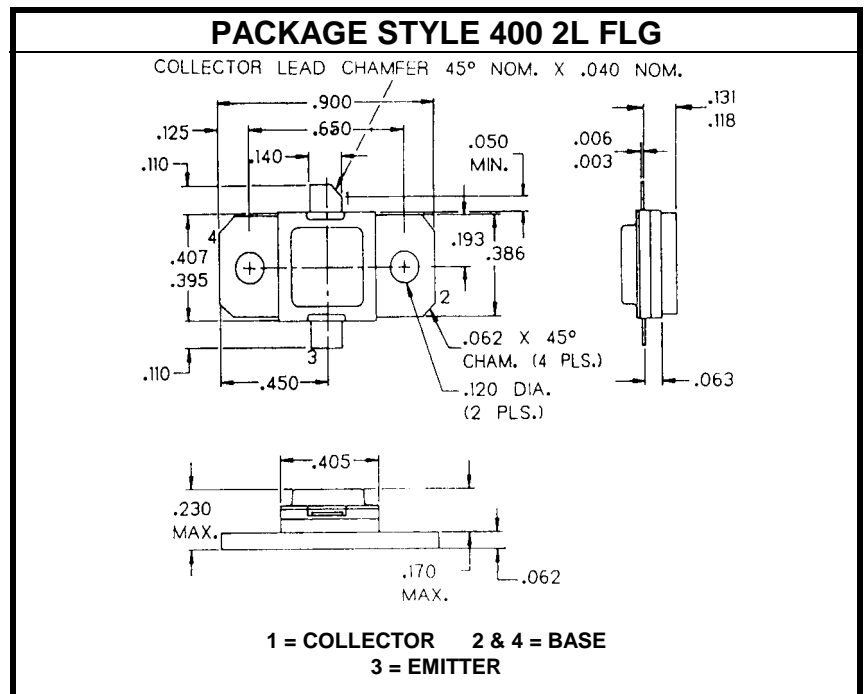
The **ASI MSC74519** is a Common Base Device Designed for Class C Applications in the 1.6 - 1.8 GHz bands.

FEATURES INCLUDE:

- Input/Output Matching
- Gold Metallization
- Hermetically Sealed Package
- Emitter Ballasting

MAXIMUM RATINGS

I_C	1.0 A
V_{CB0}	40 V
P_{DISS}	31 W @ T _C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +200 °C
θ_{JC}	5.5 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	I _C = 2.0 mA	40			V
BV_{EBO}	I _C = 2.0 mA	3.5			V
I_{CB0}	V _{CB} = 28 V			0.5	mA
h_{FE}	V _{CE} = 5 V I _C = 0.4 A	10		200	---
P_G	V _{CC} = 20 V P _{IN} = 2.0 W f = 1.6 - 1.8 GHz	6.8			dB
η_c	Pulse Width = 100 μS Duty Cycle = 10%	47			%